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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電 気 的 特 性 (T _b =25°C)										外 形	備 考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μS)	f _{αb} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 ($T_a = 25^\circ\text{C}$)				電気的特性 ($T_a = 25^\circ\text{C}$)											備考										
				V_{CBO} (V)	V_{EBO} (V)	I_C (mA)	P_C (mW)	T_j ($^\circ\text{C}$)	ICBO 最大値 (μA)		直流又はパルス h_{FE} $V_{CE}(V)$ $I_C(mA)$		バイアス $V_{CB}(V)$ $I_E(mA)$			h_{fe} h_{fb}^*	h_{ie} h_{ib}^* (Ω)	h_{re} h_{rb}^* ($\times 10^{-4}$)		h_{or} h_{ob}^* ($\mu\Omega$)	$f_{\beta b}$ f_T (Mc)	C_{ob} (pF)	r_{bb} $r_{bb(res)}$ (Ω)	外形					
2SC2382	東芝	PA	Si.EP	40	4	12A	100W ($T_c=25^\circ\text{C}$)	175	2mA	15	>10	5	10A												120	281			
" 2383	"	"	Si.E	160	6	1A	900	150	1	150	60-320	5	200	5	-200								>20*	<20	20	241	2SA1013 とコンパリ		
" 2384	"	"	"	160	6	1A	10W ($T_c=25^\circ\text{C}$)	150	1	150	60-320	5	200	5	-200								>20*	<20	20	249	2SA1014 とコンパリ		
" 2385	三菱	AF.LN.RF	Si.EP	70	5	100	200	125	0.1	50	250-1200	6	1	6	-10								$V_{NO}<300mV$ (10V, 1mA, $R_G=100k\Omega$, $A_i=80dB$)	130*	11.5	12	138B		
" 2386	"	RF	"	70	5	300	500	125	0.1	70	600	6	1	6	-10								125*	12.5	10	138B			
" 2387	日立	SW	Si.T	500	5	8A	100W ($T_c=25^\circ\text{C}$)	150	100	400	>15	5	3A													102			
" 2388	富士通	SW.PA	Si.TMe	450	5	4A	75W ($T_c=25^\circ\text{C}$)	175	100	450	20	5	2A													102			
" 2389	東洋電機	AF.LN	Si.EP	120	5	50	300	125	0.5	100	180-820	6	2	12	-2								$V_{NO}<150mV$ (10V, 1mA, $R_G=100k\Omega$, $A_i=80dB$)	140*	2.5		138	2SA1033 とコンパリ	
" 2390	"	"	"	80	5	50	300	125	0.5	75	180-820	6	2	12	-2								$V_{NO}<150mV$ (10V, 1mA, $R_G=100k\Omega$, $A_i=80dB$)	140*	2.5		138	2SA1033 とコンパリ	
" 2391	東芝	PA	"	35	3.5	800	7.5W ($T_c=25^\circ\text{C}$)	175	1mA	15	>10	5	500												<10	325			
" 2392	"	"	"	35	3.5	3.5A	30W ($T_c=25^\circ\text{C}$)	175	1mA	15	>10	5	1A												30	325			
" 2393	"	"	Si.E	80	4	4A	12.5W ($T_c=25^\circ\text{C}$)	150	15	40	50	5	2A													268			
" 2394	"	"	Si.EP	45	4	6A	20W ($T_c=25^\circ\text{C}$)	150	100	35	20-100	5	1A													268			
" 2395	"	"	"	40	4	5A	40W ($T_c=25^\circ\text{C}$)	150			>20	5	1A	5	-1A										<150	325			
" 2396	日立	AF	Si.E	60	5	100	400	125	0.1	50	250-1200	12	2	12	-2										90*	3	138	2SA1025 とコンパリ	
" 2397	"	PA	"	60	5	8A	25W ($T_c=25^\circ\text{C}$)	150	1	45	100-200	10	2A	10	-100										100	120	268		
" 2398	ソニー	PA.SW	Si.EP _a	100	5	10A	95W ($T_c=25^\circ\text{C}$)	120	10	50	>50	2	100	2	-1A										80*	240	102	2SA1028 とコンパリ	
" 2399	日立	RF	Si.EP	30	4	20	310	125	0.5	10	35-200	6	1	6	-5										940*	0.9	C_{in} 12pS	138D	
" 2400	"	SW	"	40	5	100	310	125	0.25	20	100	1	10	10	-10										1200*	1.8		138D	
" 2401	"	RF.SW	Si.P	40	10	300	310	125	0.1	30	10000	5	10	5	-10										200*	3.5	C_{in} 12pS	138D	デュリントン
" 2402	富士通	SW.PA	Si.TMe	300	7	15A	150W ($T_c=25^\circ\text{C}$)	175	100	300	20	5	5A														102		
" 2403	"	"	"	300	7	40A	300W ($T_c=25^\circ\text{C}$)	175	100	300	20	5	20A														41		
" 2404	松下	RF	Si.EP	30	3	15	100	125			>40	6	1	6	-1										650*	C_{in} 0.8	176		
" 2405	"	AF.I.V	"	35	5	50	200	125	0.1	10	180-1040	5	2														176		
" 2406	"	"	"	55	5	50	200	125	0.1	10	180-1040	5	2														176		
" 2407	日電	RF	Si.E	35	3	150	600	150	0.5	20	60	10	50													1	138C		
" 2408	"	"	"	35	3	150	600	150	0.5	20	100	10	50	10	-50											3500*	1.25	138C	
" 2409	東洋電機	AF	Si.EP	50	9	100	300	125	0.5	30	180-560	6	1	12	-2											180*	2	138	
" 2410	"	RF.I.F.Conv Mix.Osc	"	40	5	100	250	125	0.5	24	39-180	6	2	12	-2											230*	1.8	138	
" 2411	"	AF.Osc.SW	"	40	5	500	200	125	1	20	82-390	3	10	5	-20											250*	6	335	2SA1035 とコンパリ